

This listing of claims will replace all prior versions of claims in the application.

Claims 1-11. (cancelled)

Claim 12. (previously presented) A photoresist composition comprising a resin that comprises a polymer that contains pendant photoacid labile moieties and is substantially free of any aromatic groups, a photoacid generator and a non-aromatic amine compound that comprises a tertiary nitrogen alicyclic ring member.

Claim 13. (cancelled)

Claim 14. (original) A photoresist of claim 12 wherein the tertiary nitrogen ring member is at a junction position of at least two rings of a multiple ring compound.

Claim 15. (original) A photoresist of claim 12 wherein the amine compound is a bicyclic compound.

Claim 16. (currently amended) A photoresist of claim 12 wherein the tertiary nitrogen is substituted by two tertiary carbon atoms and contains from about 6 to about 24 non-hydrogen atoms.

Claim 17. (original) A photoreist of claim 12 wherein the photoacid generator compound is a non-ionic compound.

Claim 18. (previously presented) The photoresist of claim 12 wherein the resin comprises a polymer that contains pendant photoacid labile moieties and is completely free of any aromatic groups.

Claim 19. (original) A method of forming a positive photoresist relief image, comprising:

- (a) applying a coating layer of a photoresist of claim 12 on a substrate; and
- (b) exposing and developing the photoresist relief image to yield a relief image.

Claim 20. (original) The method of claim 19 wherein the photoresist layer is exposed with radiation having a wavelength of about 193 nm.

Claim 21. (previously presented) An article of manufacture comprising a microelectronic wafer or flat panel display having coated thereon a layer of the photoresist composition of claim 12.